

# HiPerFET™ Power MOSFETs

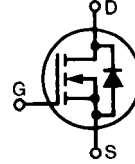
## IXFX 100N25 IXFK 100N25

$$V_{DSS} = 250 \text{ V}$$

$$I_{D25} = 100 \text{ A}$$

$$R_{DS(on)} = 27 \text{ m}\Omega$$

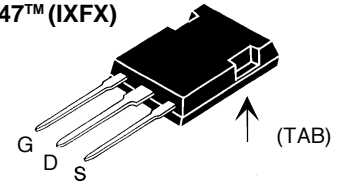
Single MOSFET Die



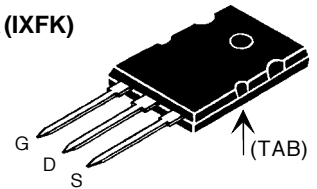
$$t_{rr} \leq 250 \text{ ns}$$

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	250	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GS} = 1 \text{ M}\Omega$	250	V
$V_{GS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$ (MOSFET chip capability)	100	A
$I_{D104}$	$T_C = 104^\circ\text{C}$ (External lead capability)	75	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	400	A
$I_{AR}$	$T_C = 25^\circ\text{C}$	100	A
$E_{AR}$	$T_C = 25^\circ\text{C}$	64	mJ
$E_{AS}$	$T_C = 25^\circ\text{C}$	3	J
$dv/dt$	$I_S \leq I_{DM}$ , $di/dt \leq 100 \text{ A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ $T_J \leq 150^\circ\text{C}$ , $R_G = 2 \Omega$	5	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	560	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	1.6 mm (0.063 in.) from case for 10 s	300	$^\circ\text{C}$
$M_d$	Mounting torque	TO-264	0.9/6 Nm/lb.in.
Weight		PLUS 247	6 g
		TO-264	10 g

PLUS 247™ (IXFX)



TO-264 AA (IXFK)



G = Gate  
S = Source

D = Drain  
TAB = Drain

### Features

- International standard packages
- Low  $R_{DS(on)}$  HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
  - easy to drive and to protect
- Fast intrinsic rectifier

### Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control
- Temperature and lighting controls

### Advantages

- PLUS 247™ package for clip or spring mounting
- Space savings
- High power density

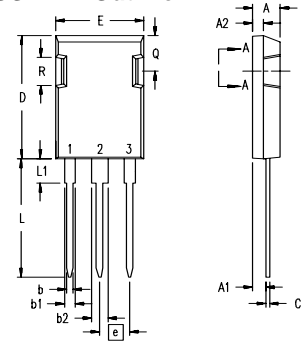
Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_{DSS}$	$V_{GS} = 0 \text{ V}$ , $I_D = 3 \text{ mA}$	250		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 8 \text{ mA}$	2.0		4.0 V
$I_{GSS}$	$V_{GS} = \pm 20 \text{ V}$ , $V_{DS} = 0$			$\pm 200 \text{ nA}$
$I_{DSS}$	$V_{DS} = V_{DSS}$			100 $\mu\text{A}$
	$V_{GS} = 0 \text{ V}$			2 mA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$ , $I_D = 0.5 I_{D25}$ Note 1			27 m $\Omega$

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$g_{fs}$	$V_{DS} = 10\text{ V}; I_D = 0.5 I_{D25}$ Note 1	40	70	S
$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		9100	pF
$C_{oss}$			1800	pF
$C_{rss}$			600	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 1\ \Omega$ (External),		42	ns
$t_r$			55	ns
$t_{d(off)}$			110	ns
$t_f$			40	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$		300	nC
$Q_{gs}$			57	nC
$Q_{gd}$			160	nC
$R_{thJC}$			0.22	K/W
$R_{thCK}$		0.15		K/W

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$I_s$	$V_{GS} = 0\text{ V}$			100 A
$I_{SM}$	Repetitive; pulse width limited by $T_{JM}$			400 A
$V_{SD}$	$I_F = I_s, V_{GS} = 0\text{ V}$ , Note 1			1.5 V
$t_{rr}$	$I_F = 50\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$			250 ns
$Q_{RM}$			1.4	$\mu\text{C}$
$I_{RM}$			10	A

Note: 1. Pulse test,  $t \leq 300\ \mu\text{s}$ , duty cycle  $d \leq 2\%$

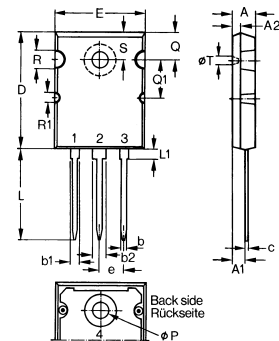
### PLUS 247™ Outline



Terminals: 1 - Gate  
2 - Drain (Collector)  
3 - Source (Emitter)  
4 - Drain (Collector)

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A <sub>1</sub>	2.29	2.54	.090	.100
A <sub>2</sub>	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b <sub>1</sub>	1.91	2.13	.075	.084
b <sub>2</sub>	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

### TO-264 AA Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A <sub>1</sub>	2.54	2.89	.100	.114
A <sub>2</sub>	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b <sub>1</sub>	2.39	2.69	.094	.106
b <sub>2</sub>	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETS and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715  
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025